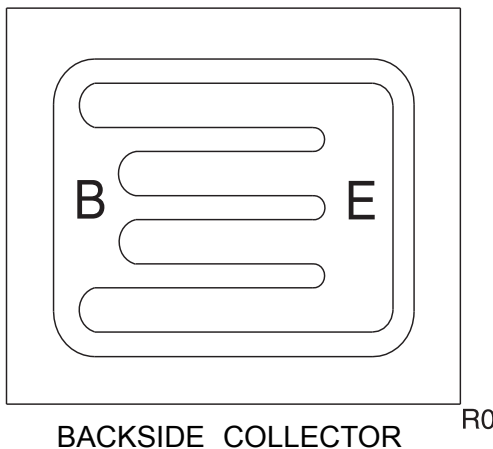


**PROCESS DETAILS**

Process	EPITAXIAL BASE
Die Size	80 x 99 MILS
Die Thickness	12.5 MILS
Base Bonding Pad Area	12 x 32 MILS
Emitter Bonding Pad Area	13 x 48 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Cr/Ni/Ag 16,000Å

**GEOMETRY**



**GROSS DIE PER 4 INCH WAFER**

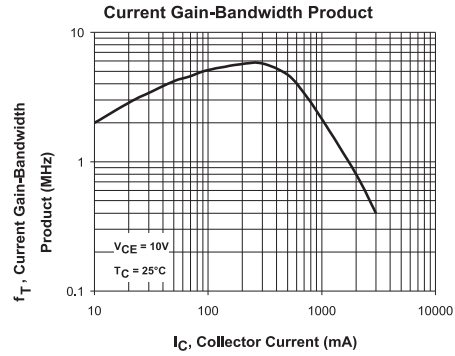
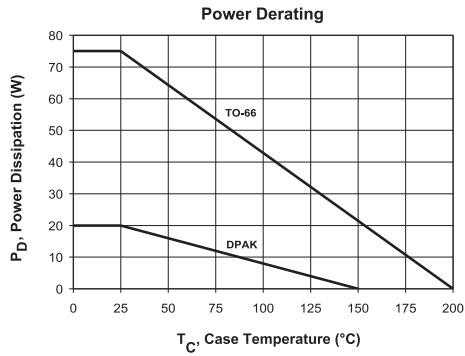
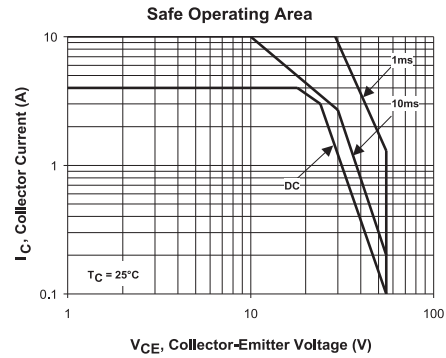
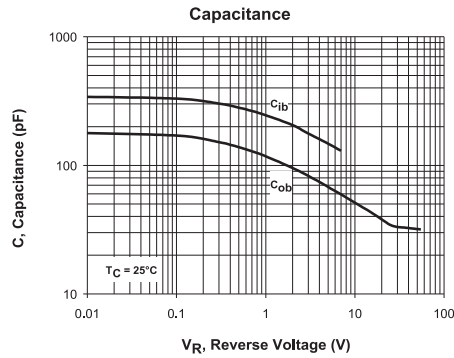
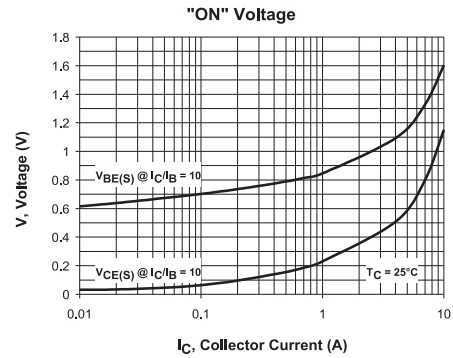
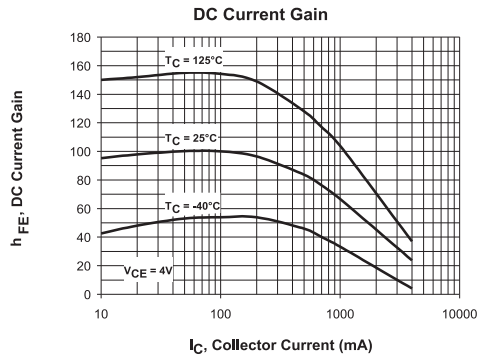
1,450

**PRINCIPAL DEVICE TYPES**

2N3054A  
CJD41C  
TIP41C

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
[www.centrasemi.com](http://www.centrasemi.com)

R3 (21-September 2003)



145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
www.centrasemi.com

R3 (21-September 2003)